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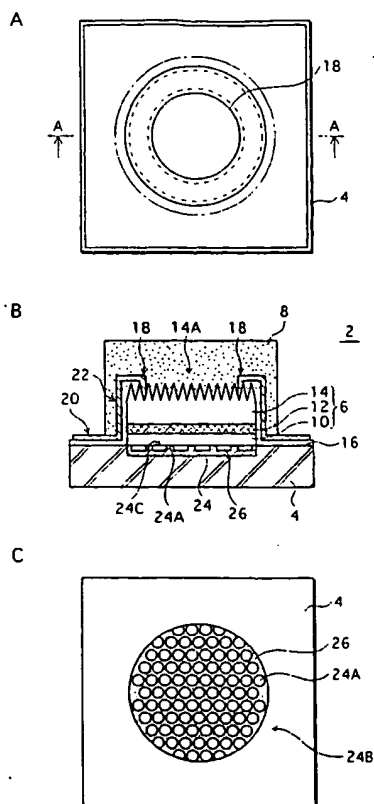
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(54) Title: NITRIDE BASED LED WITH A P-TYPE INJECTION REGION



(57) Abstract: An LED chip (2) is composed of a p-GaN layer (10), an n-GaN layer (14), and an MQW emission layer (12) that is sandwiched between the GaN layers (10 and 14). Each layer is made of a GaN semiconductor. Light exits the LED chip (2) through the n-GaN layer (14). A p-electrode (16) of the LED chip (2) has a surface profile (24B) defined by a plurality of columnar projections (24A) formed in a uniformly distributed relation on the surface facing toward the p-GaN layer (10). The p-electrode (16) is in contact with the p-GaN layer (10) at the top surface of each projection (24A).

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